RHRD440, RHRD460, RHRD440S, RHRD460S

Data Sheet | **January 2000** | **File Number 3613.5**

4A, 400V - 600V Hyperfast Diodes

The RHRD440, RHRD460, RHRD440S and RHRD460S are hyperfast diodes with soft recovery characteristics (t_{rr} < 30ns). They have half the recovery time of ultrafast diodes and are of silicon nitride passivated ion-implanted epitaxial planar construction.

These devices are intended for use as freewheeling/ clamping diodes and rectifiers in a variety of switching power supplies and other power switching applications. Their low stored charge and hyperfast soft recovery minimize ringing and electrical noise in many power switching circuits, reducing power loss in the switching transistors.

Formerly developmental type TA49055.

Features

- Hyperfast with Soft Recovery . . . . . <30ns
- Operating Temperature. . . . . 175^{o}C
- Reverse Voltage Up to 600V
- Avalanche Energy Rated
- Planar Construction

Applications

- Switching Power Supplies
- Power Switching Circuits
- General Purpose

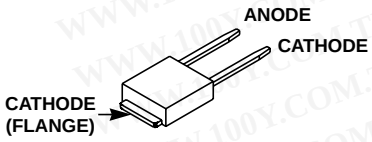
Ordering Information

PART NUMBER	PACKAGE	BRAND
RHRD440	TO-251	RHR440
RHRD460	TO-251	RHR460
RHRD440S	TO-252	RHR440
RHRD460S	TO-252	RHR460

NOTE: When ordering, use the entire part number. Add the suffix 9A to obtain the TO-252AA variant in the tape and reel, i.e., RHRD460S9A.

Packaging

JEDEC STYLE TO-251



Symbol

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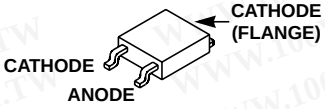
JEDEC STYLE TO-252



Absolute Maximum Ratings T_C = 25^{o}C, Unless Otherwise Specified

		RHRD440, RHRD440S	RHRD460, RHRD460S	UNITS
Peak Repetitive Reverse Voltage	V_{RRM}	400	600	V
Working Peak Reverse Voltage	V_{RWM}	400	600	V
DC Blocking Voltage	V_R	400	600	V
Average Rectified Forward Current (T_C = 157^{o}C)	$I_{F(AV)}$	4	4	A
Repetitive Peak Surge Current (Square Wave, 20kHz)	I_{FRM}	8	8	A
Nonrepetitive Peak Surge Current (Halfwave, 1 Phase, 60Hz)	I_{FSM}	40	40	A
Maximum Power Dissipation	P_D	50	50	W
Avalanche Energy (See Figures 10 and 11)	E_{AVL}	10	10	mJ
Operating and Storage Temperature	T_{STG}, T_J	-65 to 175	-65 to 175	^{o}C
Maximum Lead Temperature for Soldering (Leads at 0.063 in. (1.6mm) from case for 10s)	T_L	300	300	^{o}C
Package Body for 10s, see Tech Brief 334	T_{PKG}	260	260	^{o}C

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Electrical Specifications $T_C = 25^oC$, Unless Otherwise Specified

SYMBOL	TEST CONDITION	RHRD440, RHRD440S			RHRD460, RHRD460S			UNITS
		MIN	TYP	MAX	MIN	TYP	MAX	
V_F	I_F = 4A	-	-	2.1	-	-	2.1	V
	I_F = 4A, $T_C = 150^oC$	-	-	1.7	-	-	1.7	V
I_R	V_R = 400V	-	-	100	-	-	-	µA
	V_R = 600V	-	-	-	-	-	100	µA
	V_R = 400V, $T_C = 150^oC$	-	-	500	-	-	-	µA
	V_R = 600V, $T_C = 150^oC$	-	-	-	-	-	500	µA
t_{rr}	I_F = 1A, dI_F/dt = 200A/µs	-	-	30	-	-	30	ns
	I_F = 4A, dI_F/dt = 200A/µs	-	-	35	-	-	35	ns
t_a	I_F = 4A, dI_F/dt = 200A/µs	-	16	-	-	16	-	ns
t_b	I_F = 4A, dI_F/dt = 200A/µs	-	7	-	-	7	-	ns
Q_{RR}	I_F = 4A, dI_F/dt = 200A/µs	-	45	-	-	45	-	nC
C_J	V_R = 10V, I_F = 0A	-	15	-	-	15	-	pF
$R_{\theta JC}$		-	-	3	-	-	3	$^oC/W$

DEFINITIONS

V_F = Instantaneous forward voltage (pw = 300µs, D = 2%).

I_R = Instantaneous reverse current.

t_{rr} = Reverse recovery time (See Figure 9), summation of $t_a + t_b$.

t_a = Time to reach peak reverse current (See Figure 9).

t_b = Time from peak I_{RM} to projected zero crossing of I_{RM} based on a straight line from peak I_{RM} through 25% of I_{RM} (See Figure 9).

Q_{RR} = Reverse recovery charge.

C_J = Junction Capacitance.

$R_{\theta JC}$ = Thermal resistance junction to case.

pw = Pulse width.

D = Duty cycle.

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Typical Performance Curves

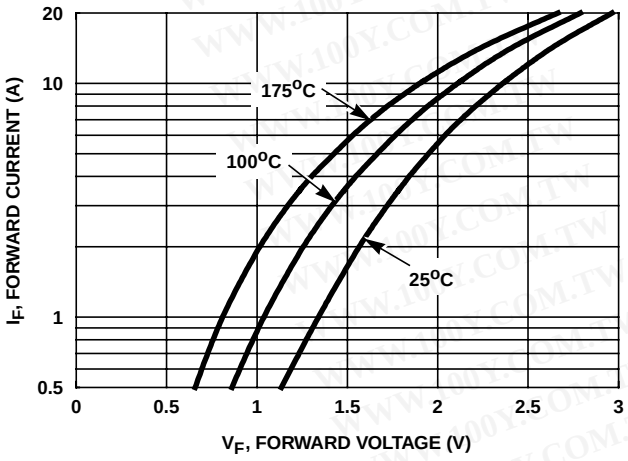

FIGURE 1. FORWARD CURRENT vs FORWARD VOLTAGE

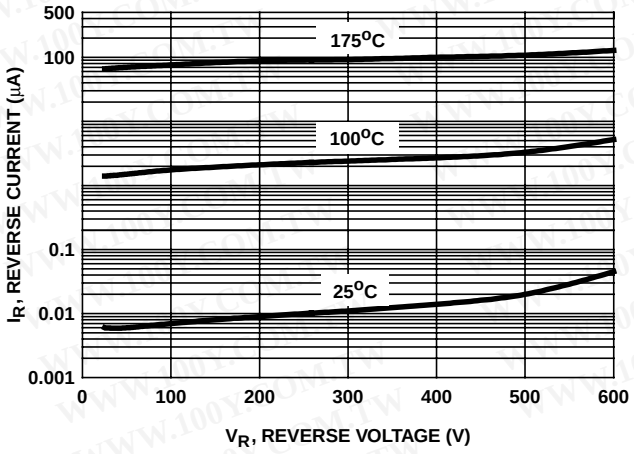

FIGURE 2. REVERSE CURRENT vs REVERSE VOLTAGE

Typical Performance Curves (Continued)

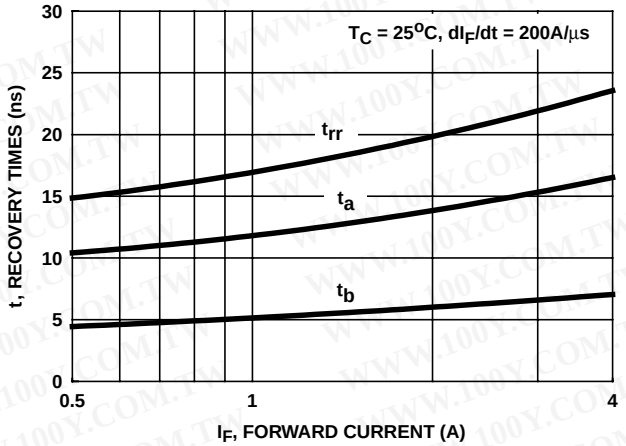

FIGURE 3. t_{rr}, t_a AND t_b CURVES vs FORWARD CURRENT

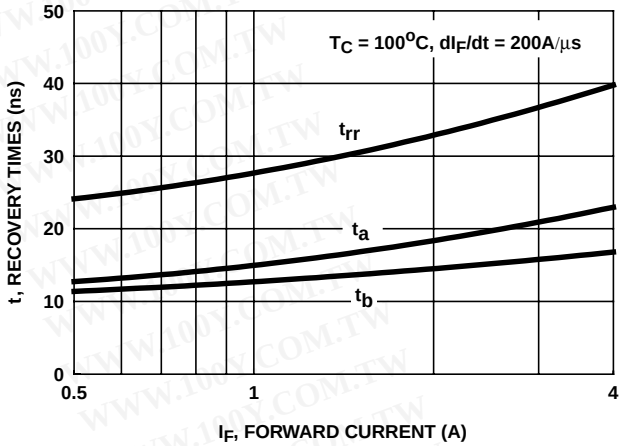

FIGURE 4. t_{rr}, t_a AND t_b CURVES vs FORWARD CURRENT

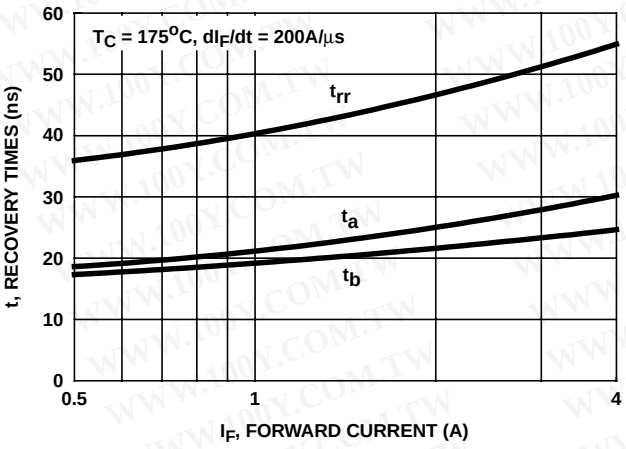

FIGURE 5. t_{rr}, t_a AND t_b CURVES vs FORWARD CURRENT

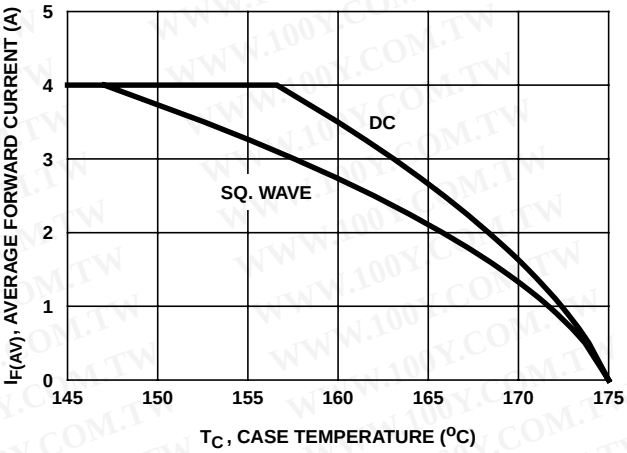

FIGURE 6. CURRENT DERATING CURVE

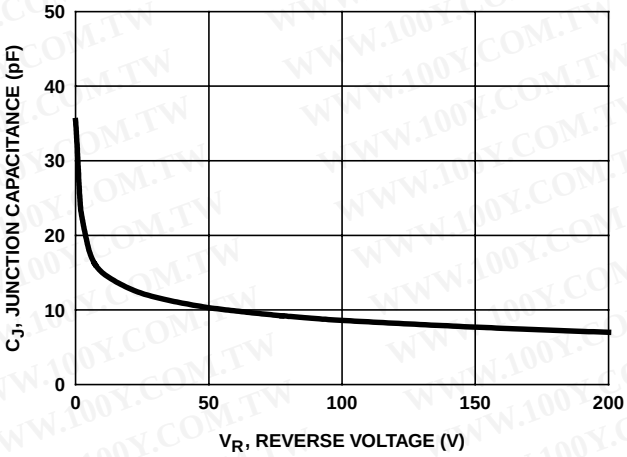

FIGURE 7. JUNCTION CAPACITANCE vs REVERSE VOLTAGE

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Test Circuits and Waveforms

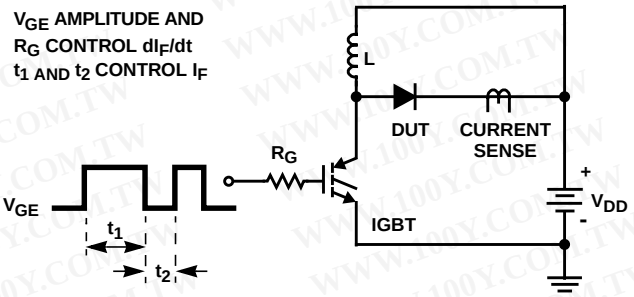

FIGURE 8. t_{rr} TEST CIRCUIT

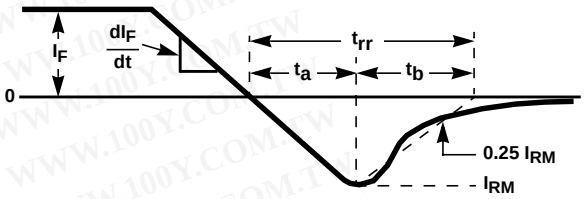

FIGURE 9. t_{rr} WAVEFORMS AND DEFINITIONS

I_{MAX} = 1A
L = 20mH
R < 0.1Ω
$E_{AVL} = 1/2LI^2 [V_{R(AVL)}/(V_{R(AVL)} - V_{DD})]$
Q_1 = IGBT (BV_{CES} > DUT $V_{R(AVL)}$)

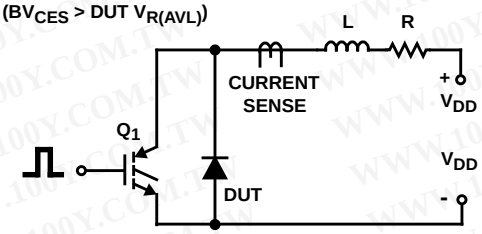

FIGURE 10. AVALANCHE ENERGY TEST CIRCUIT

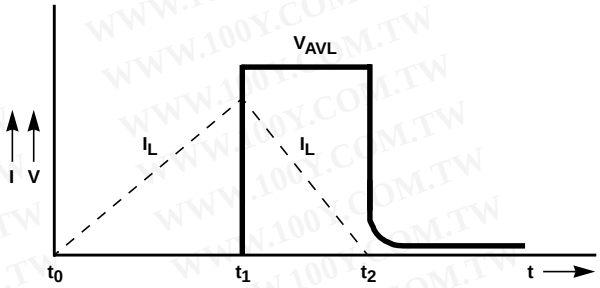

FIGURE 11. AVALANCHE CURRENT AND VOLTAGE WAVEFORMS

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